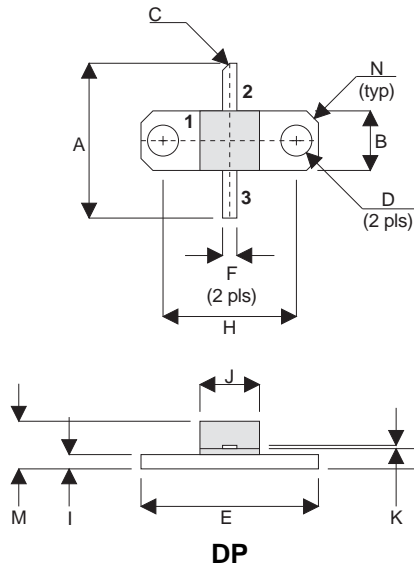


MECHANICAL DATA



PIN 1 SOURCE PIN 2 DRAIN
 PIN 3 GATE

DIM	mm	Tol.	Inches	Tol.
A	16.51	0.25	0.650	0.010
B	6.35	0.13	0.250	0.005
C	45°	5°	45°	5°
D	3.30	0.13	0.130	0.005
E	18.92	0.08	0.745	0.003
F	1.52	0.13	0.060	0.005
G	2.16	0.13	0.085	0.005
H	14.22	0.08	0.560	0.003
I	1.52	0.13	0.060	0.005
J	6.35	0.13	0.250	0.005
K	0.13	0.03	0.005	0.001
M	5.08	0.51	0.200	0.020
N	1.27 x 45°	0.13	0.050 x 45°	0.005

**GOLD METALLISED
 MULTI-PURPOSE SILICON
 DMOS RF FET
 10W – 12.5V – 1GHz
 SINGLE ENDED**

FEATURES

- SIMPLIFIED AMPLIFIER DESIGN
- SUITABLE FOR BROAD BAND APPLICATIONS
- LOW C_{rss}
- SIMPLE BIAS CIRCUITS
- LOW NOISE
- HIGH GAIN – 10 dB MINIMUM

APPLICATIONS

- VHF/UHF COMMUNICATIONS
 from DC to 1 GHz

 ABSOLUTE MAXIMUM RATINGS ($T_{case} = 25^{\circ}\text{C}$ unless otherwise stated)

P_D	Power Dissipation	42W
BV_{DSS}	Drain – Source Breakdown Voltage	40V
BV_{GSS}	Gate – Source Breakdown Voltage	$\pm 20V$
$I_{D(sat)}$	Drain Current	8A
T_{stg}	Storage Temperature	-65 to 150°C
T_j	Maximum Operating Junction Temperature	200°C

Semelab Plc reserves the right to change test conditions, parameter limits and package dimensions without notice. Information furnished by Semelab is believed to be both accurate and reliable at the time of going to press. However Semelab assumes no responsibility for any errors or omissions discovered in its use. Semelab encourages customers to verify that datasheets are current before placing orders.

ELECTRICAL CHARACTERISTICS (T_{case} = 25°C unless otherwise stated)

Parameter	Test Conditions	Min.	Typ.	Max.	Unit
B _V DSS Drain–Source Breakdown Voltage	V _{GS} = 0 I _D = 10mA	40			V
I _{DSS} Zero Gate Voltage Drain Current	V _{DS} = 12.5V V _{GS} = 0			1	mA
I _{GSS} Gate Leakage Current	V _{GS} = 20V V _{DS} = 0			1	μA
V _{GS(th)} Gate Threshold Voltage*	I _D = 10mA V _{DS} = V _{GS}	0.5		7	V
g _{fs} Forward Transconductance*	V _{DS} = 10V I _D = 0.8A	0.72			S
G _{PS} Common Source Power Gain	P _O = 10W	10			dB
η Drain Efficiency	V _{DS} = 12.5V I _{DQ} = 0.4A	40			%
VSWR Load Mismatch Tolerance	f = 1GHz	20:1			—
C _{iss} Input Capacitance	V _{DS} = 0 V _{GS} = -5V f = 1MHz			48	pF
C _{oss} Output Capacitance	V _{DS} = 12.5V V _{GS} = 0 f = 1MHz			40	pF
C _{rss} Reverse Transfer Capacitance	V _{DS} = 12.5V V _{GS} = 0 f = 1MHz			4	pF

* Pulse Test: Pulse Duration = 300 μs , Duty Cycle ≤ 2%

HAZARDOUS MATERIAL WARNING

The ceramic portion of the device between leads and metal flange is beryllium oxide. Beryllium oxide dust is highly toxic and care must be taken during handling and mounting to avoid damage to this area.

THESE DEVICES MUST NEVER BE THROWN AWAY WITH GENERAL INDUSTRIAL OR DOMESTIC WASTE.

THERMAL DATA

R _{THj-case}	Thermal Resistance Junction – Case	Max. 4.2°C / W
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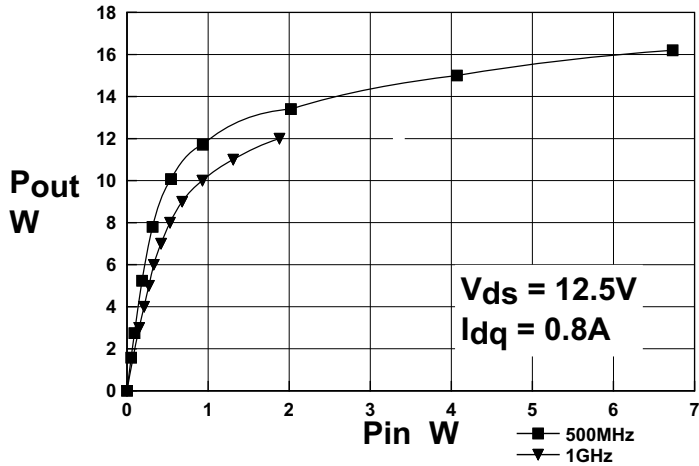


Figure 1- Power Output vs. Power Input

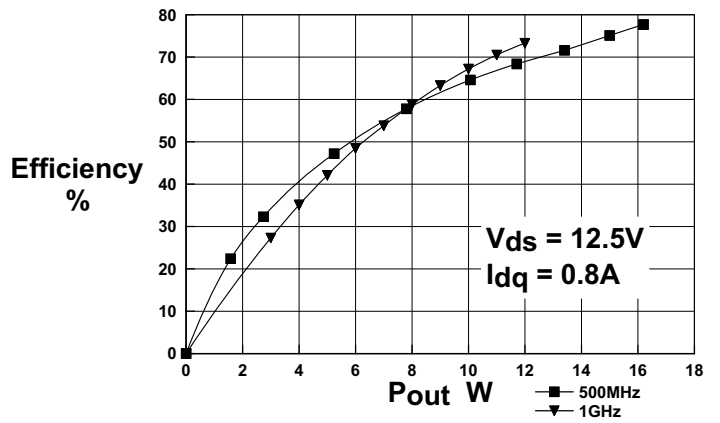


Figure 2 - Efficiency vs Output Power

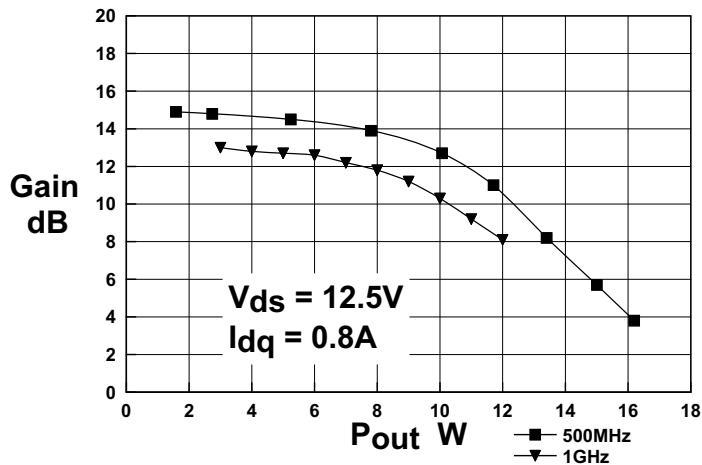


Figure 3 - Gain vs Power Output

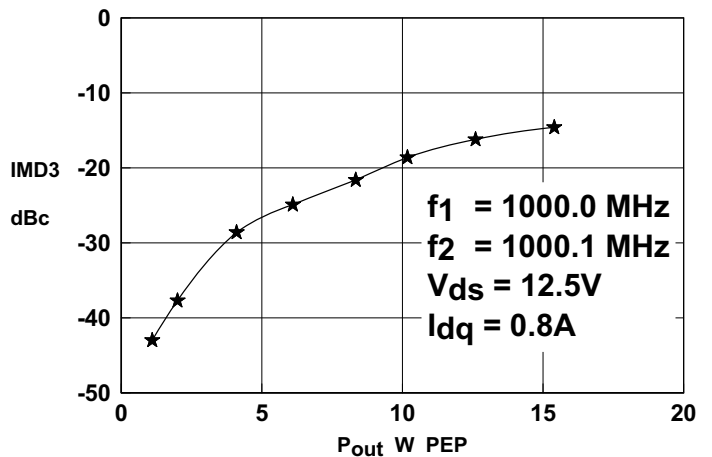


Figure 4 - IMD vs Output Power

D2212UK OPTIMUM SOURCE AND LOAD IMPEDANCE

Frequency MHz	Z_S Ω	Z_L Ω
1000MHz	$0.9 - j4.9$	$1.9 - j7.3$

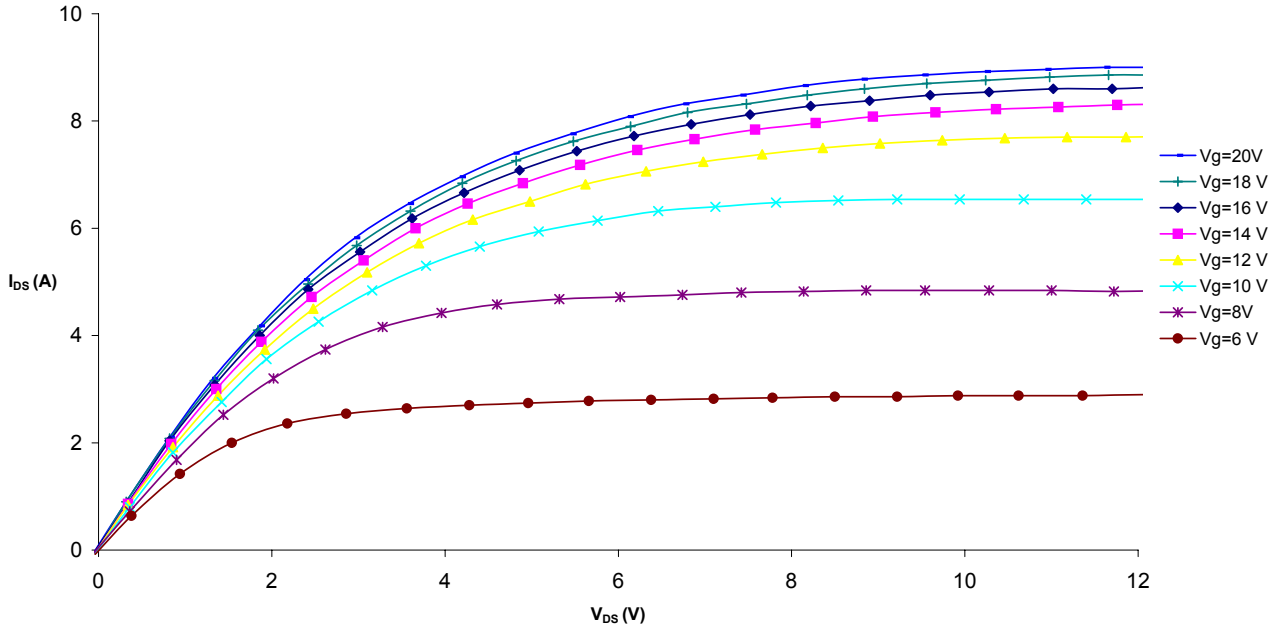


Figure 5 – Typical IV Characteristics.

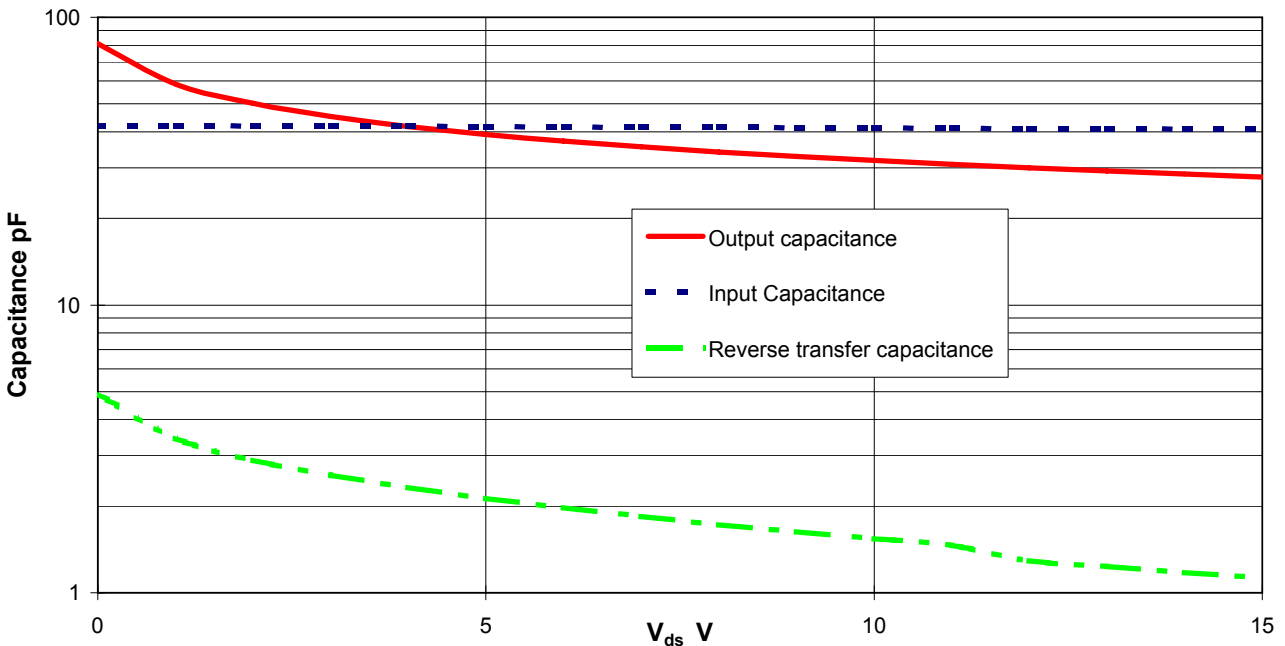
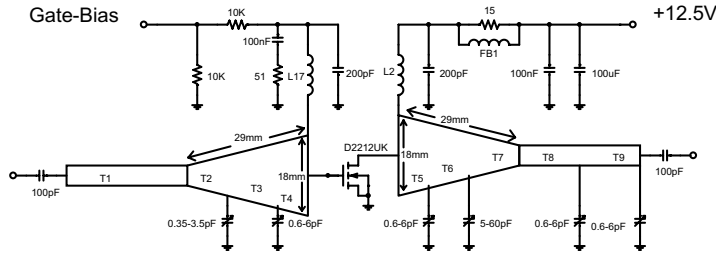


Figure 6 – Typical CV Characteristics.

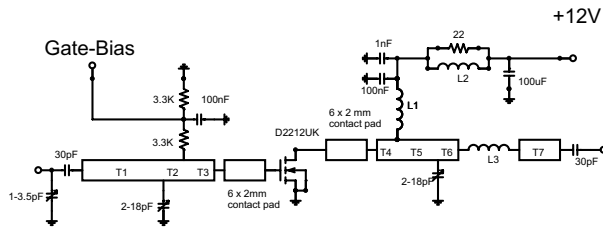
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Substrate 0.8mm PTFE/glass

- | | |
|--|-----------------|
| T1 28mm 50 Ohms | T6 14mm |
| T2 11mm | T7 10mm |
| T3 11mm | T8 11mm 50 Ohms |
| T4 7mm | T9 17mm 50 Ohms |
| T5 5mm | |
| FB1 Murata BL02RN1-R62 | |
| L1,L2 10 turns 22swg enamelled copper wire, 6mm i.d. | |

Figure 7 - 1GHz Test Fixture



Substrate 0.8mm PTFE/glass, Er=2.5

All microstrip lines W=2.2mm

- | |
|--|
| T1 32mm |
| T2 4mm |
| T3 5mm |
| T4 3mm |
| T5 9mm |
| T6 7.5mm |
| T7 13mm |
| L1 6 turns 0.5mm dia enamelled copper wire, 3mm i.d. |
| L2 1.5 turns 0.5mm enamelled copper wire on Siemens B62152A7 2 hole ferrite core |
| L3 1/16" dia wire hairpin loop 15mm long |

Figure 8 - 500MHz Test Fixture